

	1	(tungsten adj hexafluoride and silicon adj wafer) and hexamethyldisilazane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/28 14:27
-	1115557	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/28 14:28
-	205	(tungsten adj hexafluoride and silicon adj wafer) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/28 14:45
-	3	("5225366").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/28 14:45
-	8	5225366.URPN.	USPAT	2002/03/28 14:52
-	5	5294286.URPN.	USPAT	2002/03/28 15:03
-	0	5503105.URPN.	USPAT	2002/03/28 15:05
-	15	("4058430" "4389973" "4767494" "4845049" "4859627" "4876218" "4993357" "5060595" "5071670" "5130269" "5166092" "5225366" "5256244" "5270247" "5693139").PN.	USPAT	2002/03/28 15:06
-	15	heated adj wafer adj chuck	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/31 14:57
-	39	semiconductor adj wafer and chuck and heat and cool and robotic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/31 14:59
-	5233	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/07 09:20
-	41	second adj temperature and ((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/30 09:53
-	4	5130269.URPN.	USPAT	2002/08/30 09:56
-	0	micron.as. and (chemiabsorb or chemiabsorbing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/07 09:13
-	9	micron.as. and (chemisorb or chemisorbing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/07 09:14
-	6894	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/07 09:30

	0	nh2 and h20 and ((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:30
	128	precursor adj gas and ald	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 11:16
	10	(("6627260") or ("5937300") or ("6060383") or ("6258690") or ("6596636")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:28
	236	(438/628).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:36
	12	(ald or atomic adj layer adj deposition) and ((438/628).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:51
	3851	(ald or atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:51
	1158	(metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53
	315	activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53
	255	agent and (activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53
	32	semiconductor and (agent and (activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53